

# 2SC2545, 2SC2546, 2SC2547

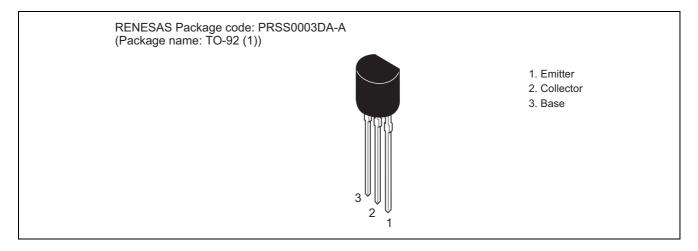
# Silicon NPN Epitaxial

REJ03G0699-0300 (Previous ADE-208-1067A) Rev.3.00 Aug.10.2005

### **Application**

Low frequency low noise amplifier

### **Outline**



### **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	2SC2545	2SC2546	2SC2547	Unit
Collector to base voltage	V <sub>CBO</sub>	60	90	120	V
Collector to emitter voltage	V <sub>CEO</sub>	60	90	120	V
Emitter to base voltage	V <sub>EBO</sub>	5	5	5	V
Collector current	Ic	100	100	100	mA
Emitter current	IE	-100	-100	-100	mA
Collector power dissipation	Pc	400	400	400	mW
Junction temperature	Tj	150	150	150	°C
Storage temperature	Tstg	-55 to +150	-55 to +150	-55 to +150	°C

# **Electrical Characteristics**

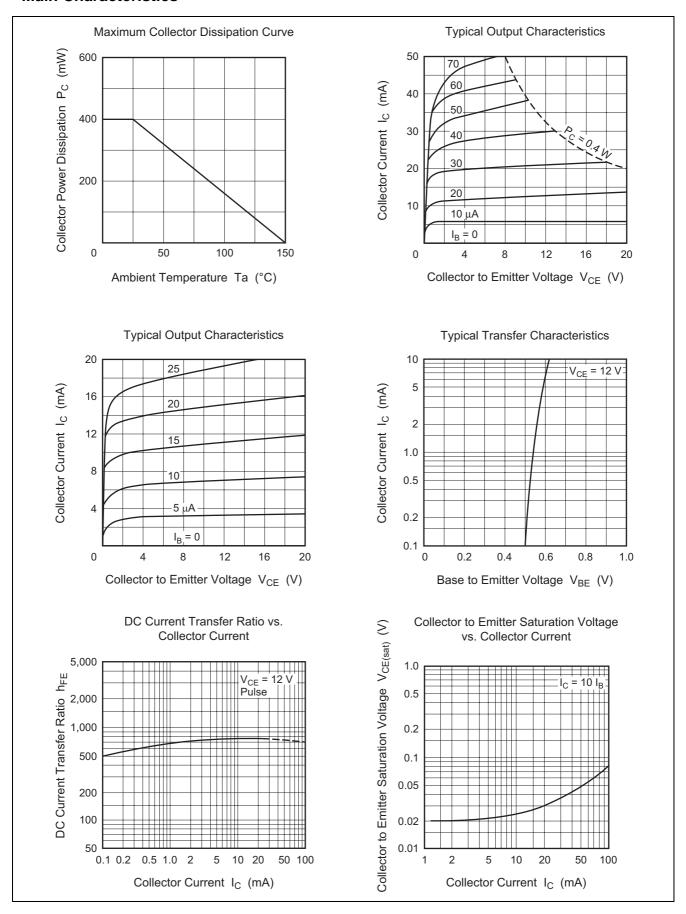
 $(Ta = 25^{\circ}C)$ 

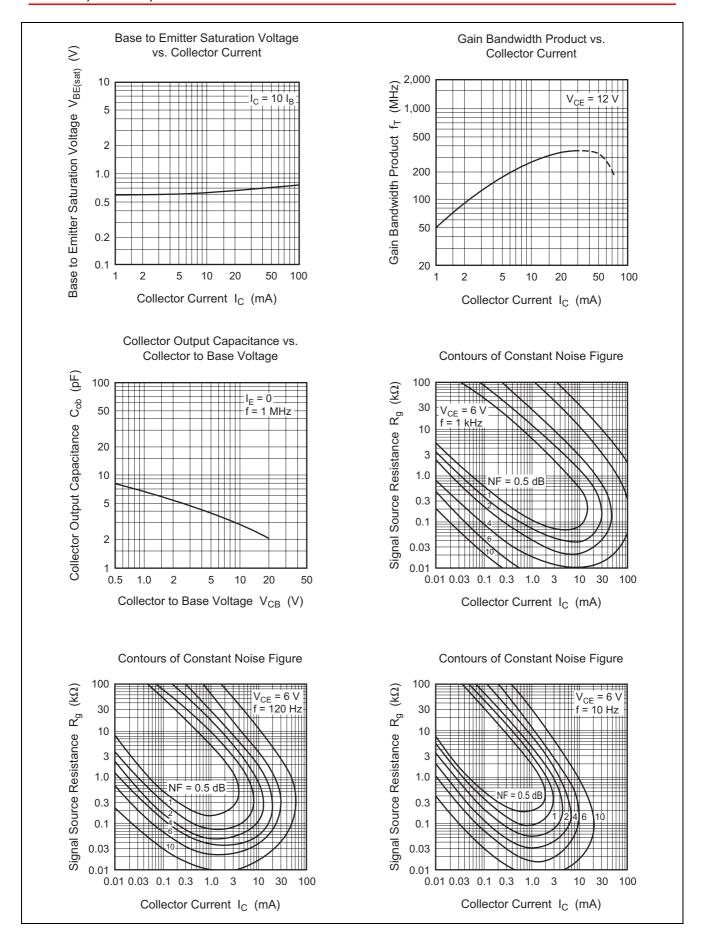
		2	SC254	15	2	SC254	6	2SC2547				
Item	Symbol	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown	V <sub>(BR)CBO</sub>	60	_	_	90	_	_	120	_	_	V	$I_C = 10 \ \mu A, \ I_E = 0$
voltage												
Collector to emitter	$V_{(BR)CEO}$	60	_	_	90	_	_	120	_	_	V	$I_C = 1 \text{ mA},$
breakdown voltage												R <sub>BE</sub> = ∞
Emitter to base breakdown	$V_{(BR)EBO}$	5	_	_	5	_	_	5	_	_	V	$I_E = 10  \mu A,  I_C = 0$
voltage												
Collector cutoff current	I <sub>CBO</sub>	_	_	0.1	l	_	0.1	_	_	0.1	μΑ	$V_{CB} = 50 \text{ V}, I_{E} = 0$
Emitter cutoff current	I <sub>EBO</sub>	_	_	0.1		_	0.1	_	_	0.1	μΑ	$V_{EB} = 2 \text{ V}, I_{C} = 0$
DC current transfer ratio	h <sub>FE</sub> *1	250	_	1200	600	_	1200	250	_	800		V <sub>CE</sub> = 12 V,
												$I_C = 2 \text{ mA}$
Collector to emitter	V <sub>CE(sat)</sub>	_	_	0.2	_	_	0.2	_	_	0.2	V	I <sub>C</sub> = 10 mA,
saturation voltage												$I_B = 1 \text{ mA}$
Base to emitter voltage	$V_{BE}$	_	0.6	_	_	0.6	_	_	0.6	_	V	V <sub>CE</sub> = 12 V,
												$I_C = 2 \text{ mA}$
Gain bandwidth product	f⊤	_	90			90	_	_	90		MHz	V <sub>CE</sub> = 12 V,
												$I_C = 2 \text{ mA}$
Collector output capacitance	Cob	_	3.0			3.0	_	_	3.0		pF	$V_{CB} = 10 \text{ V}, I_{E} = 0,$
												f = 1 MHz
Noise voltage referred input	e <sub>n</sub>	_	0.5	_	_	0.5			0.5	_	nV/	$V_{CE} = 6V$ ,
											$\sqrt{\text{Hz}}$	$I_C = 10 \text{ mA},$
												f = 1 kHz,
												$R_g = 0$ , $\Delta f = 1Hz$

Note: 1. The 2SC2545 and 2SC2547 are grouped by hFE as follows.

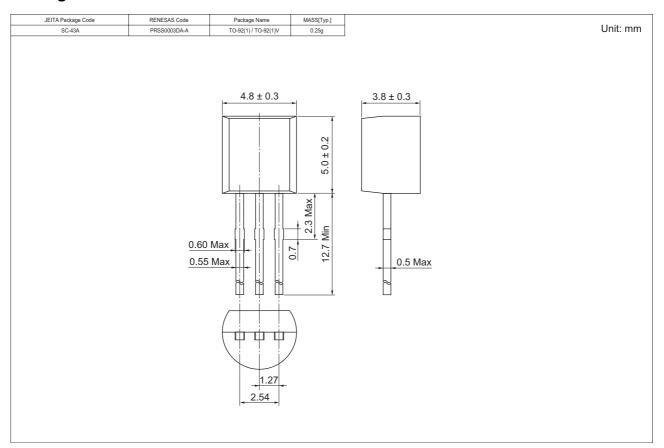
	D	E	F	
2SC2545	_	400 to 800	600 to 1200	
2SC2547	250 to 500	400 to 800	_	

### **Main Characteristics**





# **Package Dimensions**



# **Ordering Information**

Part Name Quantity		Shipping Container		
2SC2545ETZ-E	2500	Hold Box, Radial Taping		
2SC2545FTZ-E				
2SC2546FTZ-E				
2SC2547ETZ-E				

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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